FORM PTO-1449 (REV. 7-80) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO. 51889/5 US	APPLICATION NO. 10/664,666
APPLICANT – Douglas R. Hackler, Sr. et al.	
FILING DATE- September 18, 2003	

INFORMATION DISCLOSURE CITATION

Title: **MIM Multilayer Capacitor**

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
CV	1	2003/0040161 A1	02/27/03	Schrenk et al.	438	393	09/03/02
	2	2002/0192919 A1	12/19/02	Bothra	438	381	04/26/01
	3	2002/0113292 A1	08/22/02	Appel	257	532	11/08/01
	4	2002/0047154 A1	04/25/02	Sowlati et al.	257	307	04/07/00
	5	6,524,926 B1	02/25/03	Allman et al.	438	387	11/27/00
	6	6,465,832 B1	10/15/02	Maeda et al.	257	307	04/05/00
	7	6,441,419 B1	08/27/02	Johnson et al.	257	296	03/15/00
	8	6,417,535 B1	07/09/02	Johnson et al.	257	306	12/23/98
	9	6,410,955 B1	06/25/02	Baker et al.	257	307	04/19/01
	10	6,251,740 B1	06/26/01	Johnson et al.	438	381	12/23/98
	11	5,912,485	06/15/99	Chao	257	308	10/24/96
	12	5,583,359	12/10/96	Ng et al.	257	306	03/03/95
	13	5,206,787	04/27/93	Fujioka	257	307	03/27/92
CV	14	5,160,987	11/03/92	Pricer et al.	257	307	02/15/91
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EXAMINER CV DATE CONSIDERED 7/12/04

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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY / PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
	18	03091974 A	17.04.91	Japan				☐
	19							
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OTHER DOCUMENTS (Including Author, Title, Date, Relevant Pages, Place of Publication, etc.)

✓	26	Kim et al., "Development of CVD-Ru/Ta_2O_5/CVD-Ru Capacitor with Concave Structure for Multigigabit-scale DRAM Generation," 2001 IEEE, pgs. 12.1.1-12.1.4.
✓	27	Aoki et al., "Robust 130nm-Node Cu Dual Damascene Technology with Low-k Barrier SiCN," 2001 IEEE, pgs. 4.2.1-4.2.4.
✓	28	Samavati et al., "Fractal Capacitors," IEEE Journal of Solid-State Circuits, Vol. 33, No. 12, December 1998, pgs. 2035-2041.
✓	29	Kotecki et al., "(Ba, Sr) TiO dielectrics for future stacked-capacitor DRAM," IBM J. Res. Develop., Vol. 42, No. 3, May 1999, pg. 367-382.
✓	30	Media for SolidStte Technology, "Interfacial reaction and thermal stability of Ta2O5/TiN for metal electrode capacitors," http://solidstate.articles.printthis.clickability.com/pt/cpt?action=cpt&expire=&urlID=8160, 11/4/2003, pgs. 1-7.
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EXAMINER _____ DATE CONSIDERED 7/12/07

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